

09/891, 905

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,767,787 B2
DATED : July 27, 2004
INVENTOR(S) : Koh et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 6.

Line 10, should read -- A method of forming a plurality of channel regions between isolation --
Lines 26 and 27, should read -- using the mask as an implant mask, thereby forming an implant region in only the first and second portions to --
Line 29, should read -- forming a plurality of gate electrodes on the implant --
Lines 34-37, should read -- from the implant region, wherein the separate channel regions are self-aligned to the plurality of gate electrodes. --
Line 62, should read -- 8. A method of forming a plurality of channel regions between isolation --

Column 7.

Line 11, should read -- single implant region in only the first and second --
Line 14, should read -- implant region; and --
Lines 19-21, should read -- and second spaced apart channel regions from the single implant region. --

Column 8.

Line 1, should read -- A method of forming a plurality of channel regions between --
Lines 13-14, should read -- using the mask as an implant mask, thereby forming an implant region in the exposed portion of the substrate --
Line 16, should read -- forming a plurality of gate electrodes on the implant --
Lines 22-26, should read -- separate channel regions from the implant region, wherein the separate channel regions are self-aligned to the plurality of gate electrodes. --

Signed and Sealed this

First Day of February, 2005



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Director of the United States Patent and Trademark Office